

0.5 μ A I_Q, 300mA Linear Regulator

General Description

The EHP8150 features of low quiescent current as low as 0.5 μ A and almost zero disable current which is ideal for powering the battery equipment to a longer service life. The EHP8150 guarantees delivery of 300mA output current and can be stable with 1 μ F ceramic output capacitor.

The EHP8150 is available in SOT-23-3, SOT-23-5 and uDFN1X1-4 surface mount packages.

Features

- 2.5V to 5.5V input range
- 300mA output current driving capacity
- 0.5 μ A typical quiescent current at no Load
- 500mV typical dropout at I_{OUT} = 250mA
- Thermal shutdown protection
- Internal short-circuit current limit
- Stable with 1 μ F output capacitor

Ordering Information

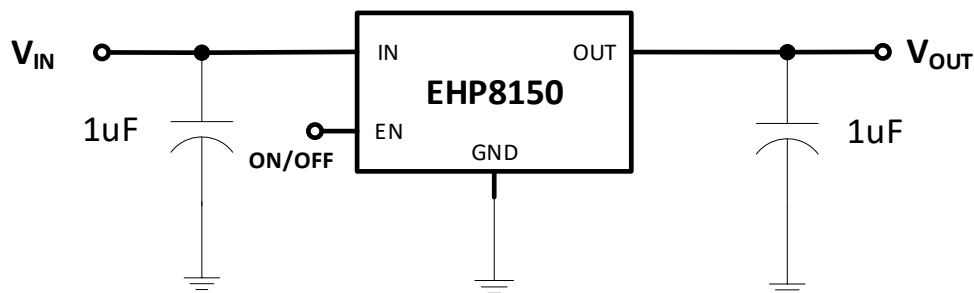
Part Number	Remark
EHP8150-XXVD03NRR	±2% output voltage tolerance
EHP8150-XXVF05NRR	±2% output voltage tolerance
EHP8150-XXDC04NRR	±2% output voltage tolerance

XX:12=1.2V, 15=1.5V, 18=1.8V, 25=2.5V, 30=3.0V, 33=3.3V

Applications

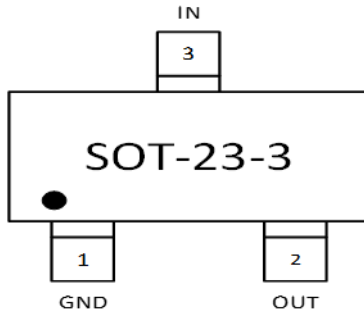
- Portable, Battery Powered Equipment
- Ultra Low Power Microcontroller
- Notebook computers

Typical Application



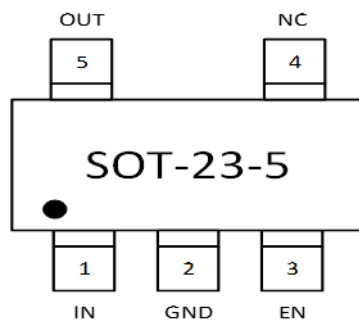
Connection Diagrams

Order information



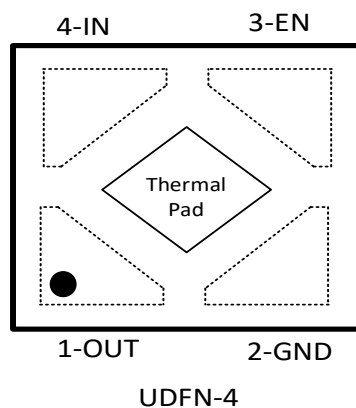
EHP8150-XXVD03NRR

XX Output voltage
VD03 SOT-23-3 Package
NRR RoHS & Halogen free package
Rating: -40 to 85°C
Package in Tape & Reel



EHP8150-XXVF05NRR

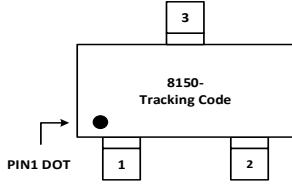
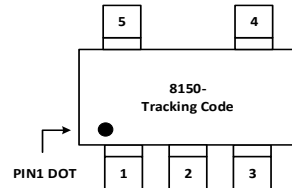
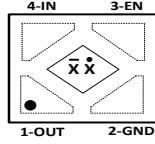
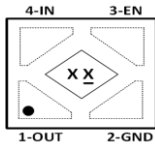
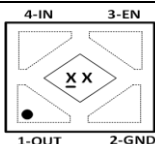
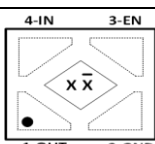
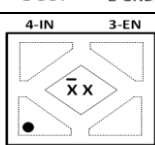
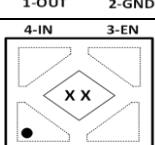
XX Output voltage
VF05 SOT-23-5 Package
NRR RoHS & Halogen free package
Rating: -40 to 85°C
Package in Tape & Reel



EHP8150-XXDC04NRR

XX Output voltage
DC04 uDFN1x1-4 Package
NRR RoHS & Halogen free package
Rating: -40 to 85°C
Package in Tape & Reel

Order, Marking and Packing Information

Package	Vout	Product ID.	Marking	Packing
SOT-23-3	1.2V	EHP8150-12VD03NRR		Tape & Reel 3K pcs
	1.5V	EHP8150-15VD03NRR		
	1.8V	EHP8150-18VD03NRR		
	2.5V	EHP8150-25VD03NRR		
	3.0V	EHP8150-30VD03NRR		
	3.3V	EHP8150-33VD03NRR		
SOT-23-5	1.2V	EHP8150-12VF05NRR		Tape & Reel 3K pcs
	1.5V	EHP8150-15VF05NRR		
	1.8V	EHP8150-18VF05NRR		
	2.5V	EHP8150-25VF05NRR		
	3.0V	EHP8150-30VF05NRR		
	3.3V	EHP8150-33VF05NRR		
uDFN-4	1.2V	EHP8150-12DC04NRR		Tape & Reel 8K pcs
	1.5V	EHP8150-15DC04NRR		
	1.8V	EHP8150-18DC04NRR		
	2.5V	EHP8150-25DC04NRR		
	3.0V	EHP8150-30DC04NRR		
	3.3V	EHP8150-33DC04NRR		

XX=tracking code

Absolute Maximum Ratings (Note1, 2)

IN, EN, OUT	-0.3V to 6V	Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature Range	-65°C to 150°C	ESD Rating	
Junction Temperature (T _J)	150°C	Human Body Model	2KV

Recommended Operating Conditions

Supply Voltage	2.5V to 5.5V	Operating Temperature Range	-40°C to 85°C
Junction Temperature Range	-40°C to 125°C		

Thermal Resistance:

Symbol	θ_{JA} (Note3)	θ_{JC} (Note4)
SOT-23-3	250(°C/W)	81(°C/W)
SOT-23-5	152(°C/W)	81(°C/W)
uDFN1x1-4	110(°C/W)	23(°C/W)

Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $V_{IN}=V_{EN}=V_{OUT}+1V$, $C_{IN}=C_{OUT}=1\mu F$, $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Output Voltage Accuracy			-2		2	%
Line Regulation	ΔV_{LINE}	$V_{IN}=V_{OUT}+1V$ to 5.5V,		20	50	mV
Load Regulation	ΔV_{LOAD}	$I_{OUT}=1mA$ to 150mA		12	30	mV
		$I_{OUT}=1mA$ to 300mA		25	60	
Dropout Voltage	V_{DROP}	$I_{OUT}=100mA$		150		mV
		$I_{OUT}=250mA$		500		mV
Quiescent Current	I_Q	No load		0.5	1	uA
Current Limit	I_{CL}			560		mA
Enable high level	V_{ENHI}		0.6			V
Enable low level	V_{ENLO}				0.2	V
Thermal Shutdown	T_{SD}			150		°C
Thermal Shutdown Hysteresis	T_{HY}			20		°C
Power-supply rejection ratio	PSRR	$f=1kHz$, $I_{OUT}=30mA$		50		dB

Note 1: Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

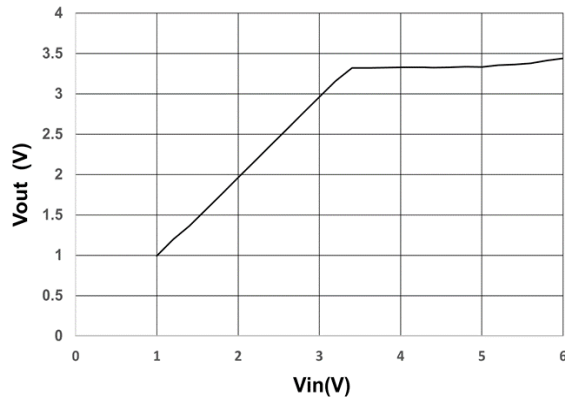
Note 2: All voltages are with respect to the potential at the ground pin.

Note 3: θ_{JA} is measured in the natural convection at $T_J=25^\circ C$ on a high effective thermal conductivity test board (2 layers, 2S0P).

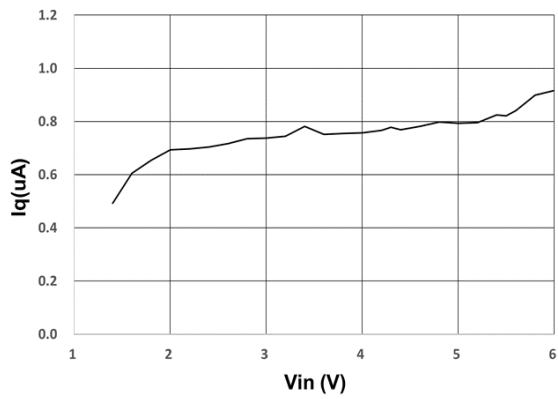
Note 4: θ_{JC} represents the resistance to the heat flows the chip to package top case.

Typical Performance Characteristics

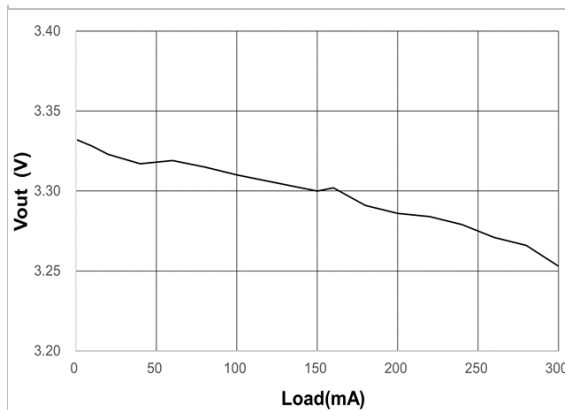
$V_{IN}=V_{OUT}+1V$, $I_{OUT}=1mA$, $V_{OUT}=3.3V$, $C_{IN}=C_{OUT}=1\mu F$, $T_a=25^{\circ}C$, unless otherwise specified



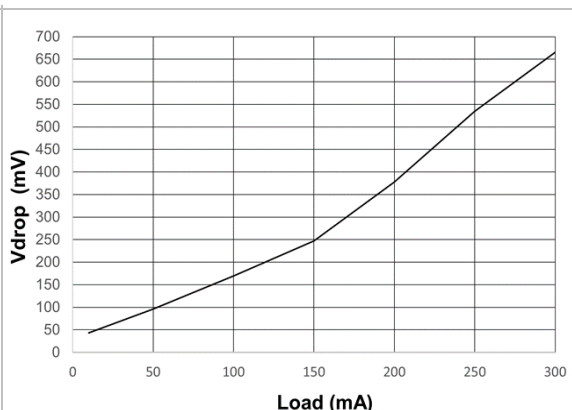
V_{OUT} vs. V_{IN} (I_{OUT} = 1mA)



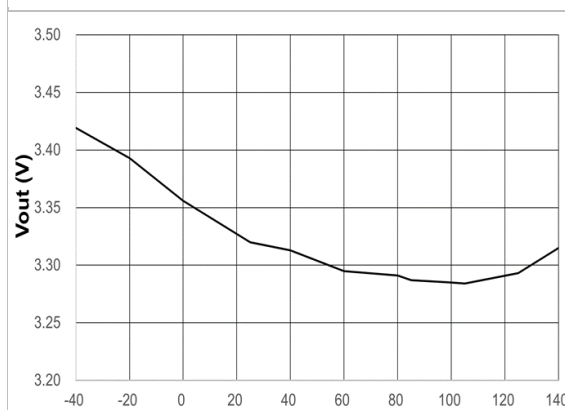
I_Q vs. V_{IN} (I_{out} = 0 mA)



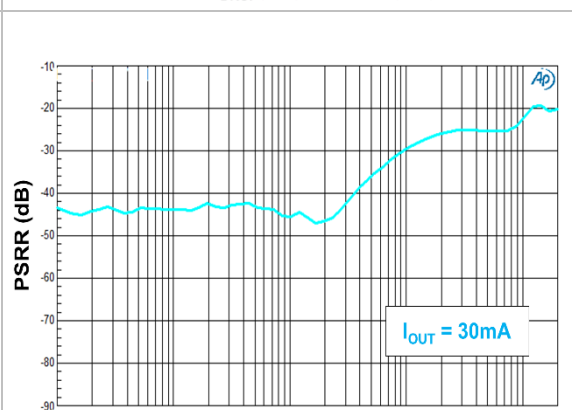
V_{OUT}(V) vs. Load(mA)



V_{DROP}(mV) vs. Load(mA)



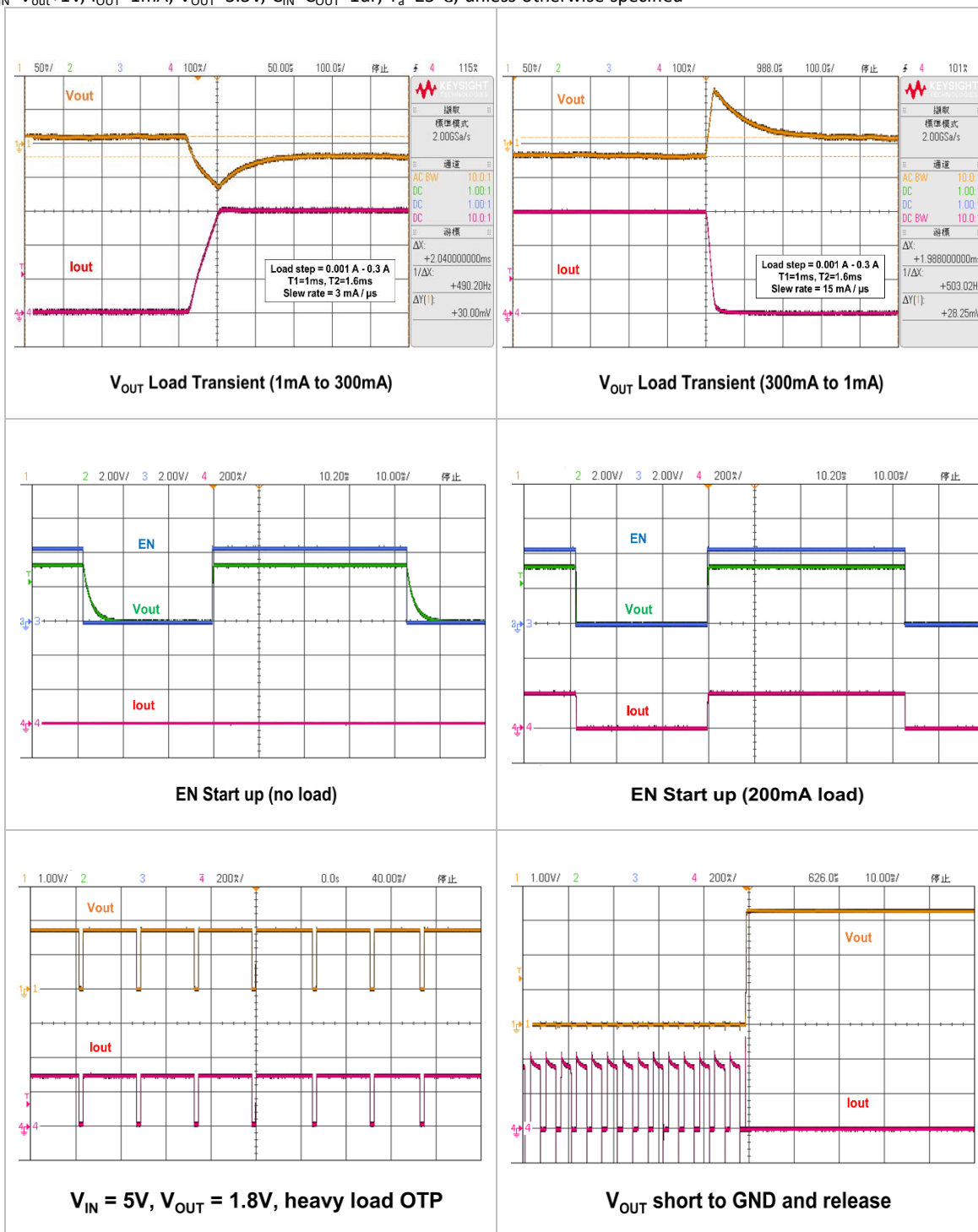
V_{OUT} vs. Ambient Temperature (I_{OUT}=1mA)



PSRR vs. Frequency (V_{IN}=4.3V, V_{OUT}=3.3V)

Typical Performance Characteristics (cont.)

$V_{IN}=V_{OUT}+1V$, $I_{OUT}=1mA$, $V_{OUT}=3.3V$, $C_{IN}=C_{OUT}=1\mu F$, $T_a=25^{\circ}C$, unless otherwise specified



Application Information

Output Capacitor

The EHP8150 is specially designed for use with ceramic output capacitors of as low as 1 μ F to take advantage of the savings in cost and space as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) is restricted to than 0.5 Ω . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as for situations where the application systems are not physically located immediately adjacent to the battery power source. Typical ceramic capacitors suitable for use with the EHP8150 are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within $\pm 20\%$ and $\pm 10\%$, respectively, as the temperature increases.

Input Capacitor

A minimum input capacitance of 1 μ F is required for EHP8150. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10 μ F tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.

Power Dissipation and Thermal Shutdown

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The EHP8150 relies on dedicated thermal shutdown circuitry to limit its total power dissipation. An IC junction temperature T_J exceeding 150 $^{\circ}$ C will trigger the thermal shutdown logic, turning off the P-channel MOS pass transistor. The pass transistor turns on again after the junction cools off by about 20 $^{\circ}$ C. When continuous thermal overload conditions persist, this thermal shutdown action then results in a pulsed waveform at the output of the regulator. The concept of thermal resistance θ_{JA} ($^{\circ}$ C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between θ_{JA} and T_J is as follows:

$$T_J = \theta_{JA} \times (P_D) + T_A$$

T_A is the ambient temperature, and P_D is the power generated by the IC and can be written as:

$$P_D = I_{OUT} (V_{IN} - V_{OUT})$$

As the above equations show, it is desirable to work with ICs whose θ_{JA} values are small such that T_J does not

increase strongly with P_D . To avoid thermally overloading the EHP8150, refrain from exceeding the recommended maximum junction temperature rating of 125°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly.

Maximum power dissipation for the device is calculated using the following equation:

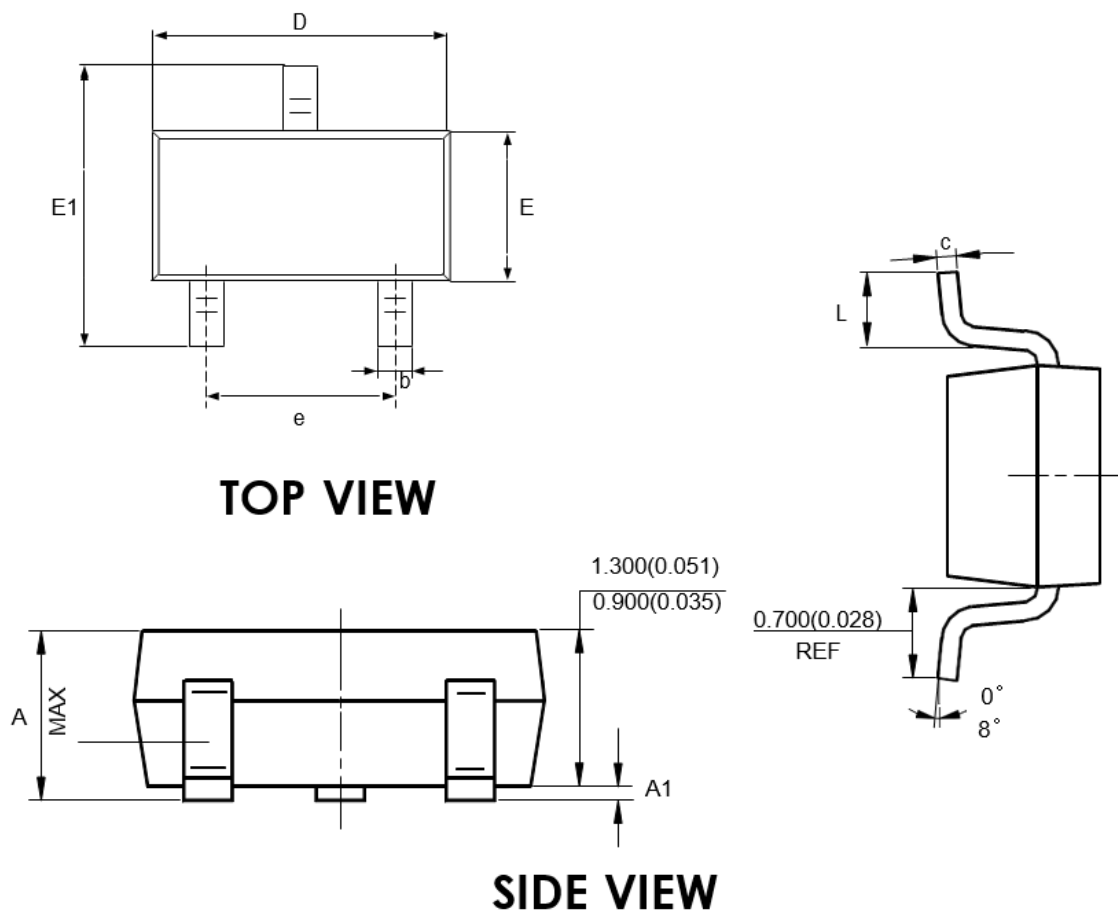
$$PD = \frac{T_{J(max)} - T_A}{\theta_{JA}}$$

Where $T_{J(max)}$ is the recommended maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance. For example,

- SOT-23-3 package, $\theta_{JA}=250^{\circ}\text{C/W}$, $T_{J(max)}=125^{\circ}\text{C}$ and using $T_A=25^{\circ}\text{C}$, the maximum power dissipation is 0.4W.
- SOT-23-5 package, $\theta_{JA}=152^{\circ}\text{C/W}$, $T_{J(max)}=125^{\circ}\text{C}$ and using $T_A=25^{\circ}\text{C}$, the maximum power dissipation is 0.65W.
- uDFN1x1-4 package, $\theta_{JA}=110^{\circ}\text{C/W}$, $T_{J(max)}=125^{\circ}\text{C}$ and using $T_A=25^{\circ}\text{C}$, the maximum power dissipation is 0.9W.

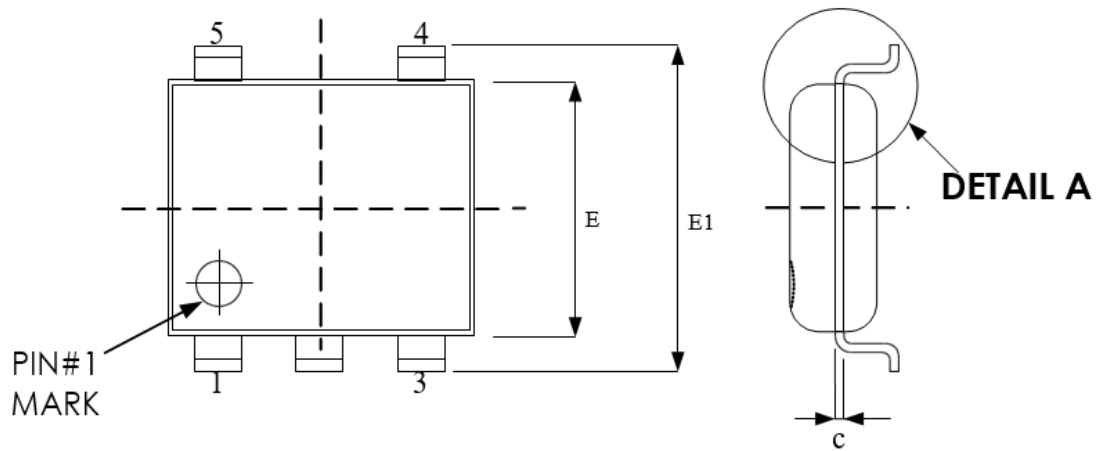
Shutdown

The EHP8150 enters the sleep mode when the EN pin is low. When this occurs, the pass transistor, the error amplifier, and the biasing circuits, including the bandgap reference, are turned off, thus reducing the supply current to typically 0.5μA. Such a low supply current makes the EHP8150 best suited for battery-powered applications. The maximum guaranteed voltage at the EN pin for the sleep mode to take effect is 0.2V.

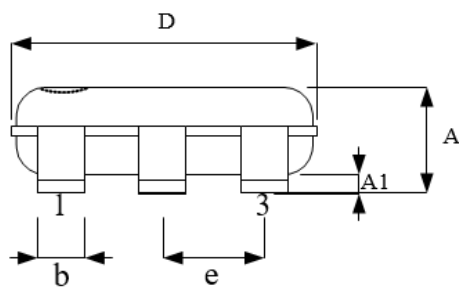
Package Outline Drawing
SOT-23-3

Symbol	Dimension in mm	
	Min.	Max.
A	0.90	1.45
A1	0.00	0.15
b	0.30	0.50
c	0.10	0.20
D	2.82	3.10
E	1.50	1.70
E1	2.65	3.00
e	1.80	2.00
L	0.30	0.60

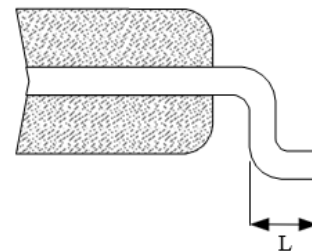
Package Outline Drawing SOT-23-5



TOP VIEW



SIDE VIEW

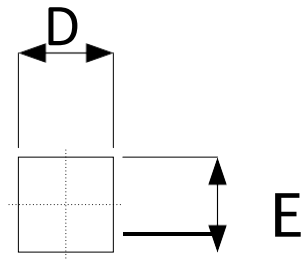


DETAIL A

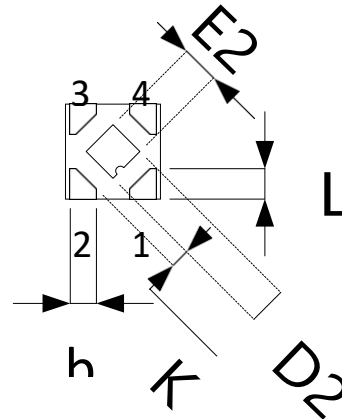
Symbol	Dimension in mm	
	Min.	Max.
A	0.90	1.45
A1	0.00	0.15
b	0.30	0.50
c	0.08	0.25
D	2.70	3.10
E	1.40	1.80
E1	2.60	3.00
e	0.95 BSC	
L	0.30	0.60

Package Outline Drawing

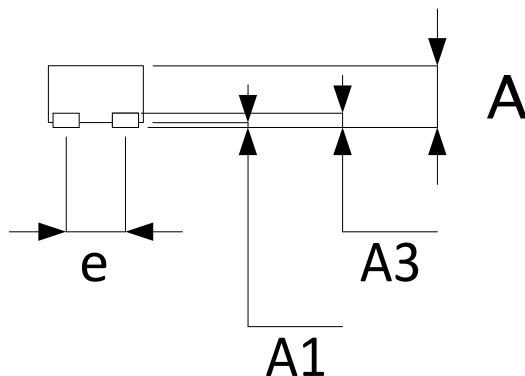
uDFN-4L (1mm x 1mm)



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Dimension in mm	
	Min	Max
A	0.35	0.60
A1	0.00	0.05
A3	0.12 REF.	
b	0.175	0.275
D	1.00 BSC	
E	1.00 BSC	
e	0.625 BSC	
L	0.200	0.300
K	0.20	-

Exposed pad

	Dimension in mm	
	Min	Max
D2	0.40	0.60
E2	0.40	0.60

Revision History

Revision	Date	Description
1.0	2024.03.05	Original

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